

CERTIFICATE OF MAILING BY "FIRST CLASS MAIL"

Thereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313 450, on August 13, 2003.

Mei/Leung

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Shigetoshi ITO and Yuhzoh TSUDA

Serial No.: 10/616,767

Filing Date: July 9, 2003

For: NITRIDE SEMICONDUCTOR LASER

DEVICE AND OPTICAL PICKUP

APPARATUS THEREWITH

Examiner: Not Yet Assigned

Group Art Unit: Not Yet Assigned

## INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97 & 1.98

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. § 1.97 and § 1.98, Applicants submit for consideration in the above-identified application the documents listed on the attached Form PTO-1449. Copies of the documents were previously submitted in an Information Disclosure Statement and/or Office Action, directed to the related application Serial Number 09/842,447, filed April 26, 2001, and, accordingly, copies are not included herewith. This protocol conforms with 37 C.F.R. §1.98(d)

and M.P.E.P. 609(A)(2). The Examiner is requested to make these documents of record in the application.

	This Inf	ormation Disclosure Statement is submitted:				
	With the application; accordingly, no fee or separate requirements are required.					
	Before	Before the mailing of a first Office Action after the filing of a Request for Continued				
	Exami	nation under § 1.114.				
$\boxtimes$	Within three months of the application filing date or before mailing of a first Office					
	Action	on the merits; accordingly, no fee or separate requirements are required.				
	After receipt of a first Office Action on the merits but before mailing of a final Office					
	Action or Notice of Allowance.					
		A fee is required. A check in the amount of is enclosed.				
		A fee is required. Accordingly, a Fee Transmittal form (PTO/SB/17) is attached				
		to this submission in duplicate.				
		A Certification under 37 C.F.R. § 1.97(e) is provided below; accordingly; no fee				
		is believed to be due.				
	After mailing of a final Office Action or Notice of Allowance, but before payment of the					
	issue	fee.				
		A Certification under 37 C.F.R. § 1.97(e) is provided below and a check in the				
		amount of is enclosed.				
		A Certification under 37 C.F.R. § 1.97(e) is provided below and a Fee Transmittal				
		form (PTO/SB/17 is attached to this submission in duplicate.)				

Applicants would appreciate the Examiner initialing and returning the Form PTO-1449, indicating that the information has been considered and made of record herein.

The information contained in this Information Disclosure Statement under 37 C.F.R. § 1.97 and § 1.98 is not to be construed as a representation that: (i) a complete search has been made; (ii) additional information material to the examination of this application does

not exist; (iii) the information, protocols, results and the like reported by third parties are accurate or enabling; or (iv) the above information constitutes prior art to the subject invention.

In the unlikely event that the transmittal form is separated from this document and the Patent Office determines that an extension and/or other relief is required, Applicants petition for any required relief including extensions of time and authorize the Assistant Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952** referencing 245402002701. However, the Assistant Commissioner is not authorized to charge the cost of the issue fee to the Deposit Account.

Dated: August 12, 2003

Respectfully submitted,

Christopher B. Eide

Registration No. 48,375

Morrison & Foerster LLP 755 Page Mill Road

Palo Alto, California 94304-1018

Telephone: (650) 813-5720 Facsimile: (650) 494-0792

## Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

	Sheet I of I			
Docket Number 245402002701	Application Number 10/616,767			
Applicant				
Shigetoshi IT	O and Yuhzoh TSUDA			
Filing Date July 9, 2003	Group Art Unit Not Yet Assigned			
Mailing Date August 47 2003				

## U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
· <u>········</u>	1.	04/25/2002	2002/0048302	Kimura			
•	2.	05/16/2002	2002/0056836	Sawazaki et al.		-	
	3.	07/04/2002	2002/0084452	Ota et al.			
	4.	07/04/2002	2002/0085603	Okumura			
	5.	02/03/1998	5,714,772	Fang et al.			
	6.	04/14/1998	5,739,554	Edmond et al.			
	7.	01/09/2001	6,172,382	Nagahama et al.			
	8.	05/15/2001	6,232,623	Morita			
	9.	12/11/2001	6,329,667	Ota et al.			

## FOREIGN PATENT DOCUMENTS

No.			Country	Class	Subclass	YES	lation NO		
10.	01/26/1998	11-214788	Japan						
OTHER DOCUMENTS (including author, title, Date, Pertinent Pages, Etc.)									
Examiner Ref. Title Initials No.									
11. Kuramoto et al. (1999) "Room-Temperature Continuous-Wave Operation of InGaN Multi-Qua Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact," <i>Jpn. J. Appl. Phy</i> L184-186.							puantum- Phys. 38:		
12.	Nakamura et al. (1998) "InGaN/GaN/A1GaN-Based Laser Diodes Grown on GaN Substrates with a Fundamental Transverse Mode," <i>Jpn. J. Appl. Phys.</i> 37: L1020-1022.								
1 1	Ref. No.	Ref. Title No.  Kuramoto et Well Laser I L184-186.  Nakamura et	OTHE  Ref. Title  No.  Kuramoto et al. (1999) "Room-7  Well Laser Diodes Grown on an L184-186.  Nakamura et al. (1998) "InGaN/6	OTHER DOCUMENTS  Ref. Title No.  Kuramoto et al. (1999) "Room-Temperature Continuous Well Laser Diodes Grown on an n-GaN Substrate with a L184-186.  Nakamura et al. (1998) "InGaN/GaN/A1GaN-Based Laser Diodes Grown on an n-GaN Substrate with a L184-186.	OTHER DOCUMENTS (include No. )  Ref. Title  No.   Kuramoto et al. (1999) "Room-Temperature Continuous-Wave Oper Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-CL184-186.   Nakamura et al. (1998) "InGaN/GaN/A1GaN-Based Laser Diodes Grown on the Classer Diodes Grown	OTHER DOCUMENTS  (including author, title, Date of the No.)  Ref. Title  No.  Kuramoto et al. (1999) "Room-Temperature Continuous-Wave Operation of InGal Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact," Jpn. L184-186.  Nakamura et al. (1998) "InGaN/GaN/A1GaN-Based Laser Diodes Grown on GaN in GaN i	OTHER DOCUMENTS (including author, title, Date, Pertinent  Ref. Title  No.  Kuramoto et al. (1999) "Room-Temperature Continuous-Wave Operation of InGaN Multi-Q Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact," Jpn. J. Appl. I L184-186.  Nakamura et al. (1998) "InGaN/GaN/A1GaN-Based Laser Diodes Grown on GaN Substrates		

DATE CONSIDERED:

Class

Subclass

Translation

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.